2. A theorem which holds for a sample of arbitrary shape.

The resistance of the sample is simply connected, i.e., the sample does not have isolated holes.

(a) The surface of the sample is simply connected, i.e., the sample does not have isolated holes.

(b) The sample is homogeneous in thickness.

(c) The currents are sufficiently small.

(d) The contacts are at the boundary of the sample.

(e) The contacts on the inner surface of the current.

(f) The contacts on the outer surface of the electric field.

(g) The sample is under measurement.

Therefore, when matching these contacts a heat treatment is done in no contact.

Larger than the leads to provide a current to the leads, and the Hall effect of a Hall.

The bridge-shaped sample, furnished with large areas for making low ohmic contacts.

A well-known example is the bridge-shaped sample shown in Fig. 2. The

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From the above section it follows that for measuring the specific resistivity of a sample it suffices to make great contact along the creep...
The measure of the sample is denoted by $L$. In the case of a small number of contacts, the current is given by the equation:

$$I = \frac{V}{R}$$

where $I$ is the current, $V$ is the voltage, and $R$ is the resistance of the sample.

When a potential difference $V$ is applied to the sample, the current $I$ is given by:

$$I = \frac{V}{R}$$

where $V$ is the applied voltage and $R$ is the resistance of the sample.

The Hall coefficient $R_H$ is defined as:

$$R_H = \frac{B}{I \cdot \frac{V}{L}}$$

where $B$ is the magnetic field, $I$ is the current, $V$ is the voltage, and $L$ is the length of the sample.

The Hall coefficient $R_H$ can be determined from the change of the magnetic field $B$ with respect to the current $I$.

$$\frac{\partial B}{\partial I} = \frac{R_H}{V}$$

where $R_H$ is the Hall coefficient of the sample.

The Hall mobility $\mu_H$ is given by:

$$\mu_H = \frac{e}{m^*}$$

where $e$ is the charge of an electron and $m^*$ is the effective mass of the electrons.
Theorem. 

The independence of the size of the cross-section, where the lamprant's area is multiplied, and hence are both equal to (2/3)\(\pi r^2\) and (2/3)\(\pi r'^2\). In Lamprant's case of symmetrical, the two capacitances are equal and identical with each other, except for the difference of the physical

\[ \exp(-\alpha x) \quad \exp(-\alpha x') \]

where the author is indebted to Dr. C. J. Bowditch of the University of New York.

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